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NTE6248 Silicon Fast Rectifier

Features:

- High Reliability
- Low Forward Voltage Drop
- High Current Capability
- High Surge Current Capability

Maximum Ratings and Electrical Characteristics:

($T_A = +25^\circ\text{C}$ unless otherwise specified. Resistive or inductive load.)

Maximum Recurrent Peak Reverse Voltage, V_{RRM}	600V
Maximum Average Rectified Forward Current (.375 (9.5) Lead Length, $T_C = +100^\circ\text{C}$), $I_{F(AV)}$.	16A
Non-Repetitive Peak Forward Surge Current (8.3ms Single Half Sine-Wave), I_{FSM}	250A
Power Dissipation, P_D	7.81W
Maximum Instantaneous Forward Voltage ($I_F = 16\text{A}$), V_F	1.5V
Maximum DC Reverse Current (Rated DC Blocking Voltage), I_R	
$T_A = +25^\circ\text{C}$	10 μA
$T_A = +100^\circ\text{C}$	500 μA
Maximum Reverse Recovery Time (Note 1), t_{rr}	50ns
Total Capacitance (Note 2), C_T	145pF
Thermal Resistance, Junction-to-Ambient, R_{thJA}	16 $^\circ\text{C/W}$
Thermal Resistance, Junction-to-Lead, R_{thJL}	1.2 $^\circ\text{C/W}$
Operating Junction Temperature Range, T_J	-65 $^\circ$ to +150 $^\circ\text{C}$
Storage Temperature Range, T_{stg}	-65 $^\circ$ to +150 $^\circ\text{C}$

Note 1. Reverse Recovery Test Conditions: $I_F = 500\text{mA}$, $I_R = 1\text{A}$, $I_{RR} = 250\text{mA}$.

Note 2. Measured at 1MHz and applied reverse voltage of 4V.

